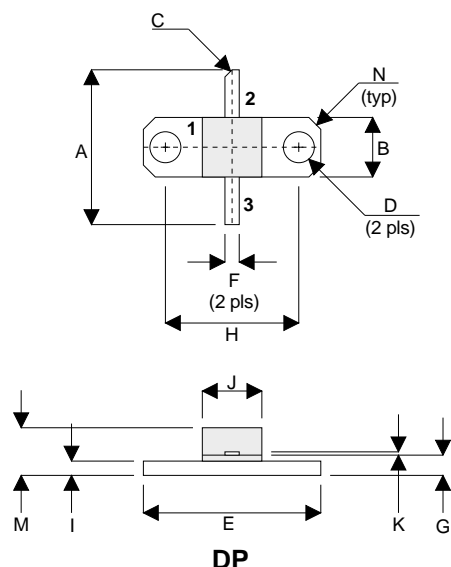


## MECHANICAL DATA



PIN 1 SOURCE PIN 2 DRAIN  
PIN 3 GATE

DIM	Millimetres	Tol.	Inches	Tol.
A	16.51	0.25	0.650	0.010
B	6.35	0.13	0.250	0.005
C	45°	5°	45°	5°
D	3.30	0.13	0.130	0.005
E	18.92	0.05	0.745	0.002
F	1.52	0.13	0.060	0.005
G	2.16	0.13	0.085	0.005
H	14.22	0.05	0.560	0.002
I	1.52	0.13	0.060	0.005
J	6.35	0.13	0.250	0.005
K	0.10	0.02	0.004	0.001
M	5.08	0.51	0.200	0.02
N	1.27 x 45°	0.13	0.050 x 45°	0.005

# GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 5W – 12.5V – 1GHz SINGLE ENDED

## FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

## APPLICATIONS

- VHF/UHF COMMUNICATIONS  
from 1 MHz to 2 GHz

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	29W
$BV_{DSS}$	Drain – Source Breakdown Voltage	40V
$BV_{GSS}$	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	4A
$T_{stg}$	Storage Temperature	$-65$ to $150^{\circ}C$
$T_j$	Maximum Operating Junction Temperature	$200^{\circ}C$

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
B <sub>V</sub> DSS Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0 I <sub>D</sub> = 10mA	40			V
I <sub>D</sub> SS Zero Gate Voltage Drain Current	V <sub>DS</sub> = 12.5V V <sub>GS</sub> = 0			2	mA
I <sub>G</sub> SS Gate Leakage Current	V <sub>GS</sub> = 20V V <sub>DS</sub> = 0			1	μA
V <sub>GS(th)</sub> Gate Threshold Voltage*	I <sub>D</sub> = 10mA V <sub>DS</sub> = V <sub>GS</sub>	1		7	V
g <sub>fs</sub> Forward Transconductance*	V <sub>DS</sub> = 10V I <sub>D</sub> = 0.2A	0.36			mhos
G <sub>PS</sub> Common Source Power Gain	P <sub>O</sub> = 5W	10			dB
η Drain Efficiency	V <sub>DS</sub> = 12.5V I <sub>DQ</sub> = 0.2A	40			%
VSWR Load Mismatch Tolerance	f = 1GHz	20:1			—
C <sub>iss</sub> Input Capacitance	V <sub>DS</sub> = 0V V <sub>GS</sub> = -5V f = 1MHz			24	pF
C <sub>oss</sub> Output Capacitance	V <sub>DS</sub> = 12.5V V <sub>GS</sub> = 0 f = 1MHz			20	pF
C <sub>rss</sub> Reverse Transfer Capacitance	V <sub>DS</sub> = 12.5V V <sub>GS</sub> = 0 f = 1MHz			2	pF

\* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

## HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

## THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 6.0°C / W
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